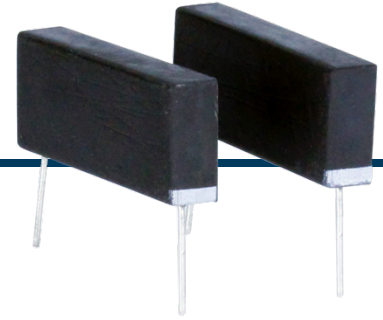




HV458 SERIES

8 to 15kV, 275 to 650mA, 75nS to Standard Recovery
High Voltage Modules



Features

- Encapsulated High Current Rectifier Module
- Large Surface Area for Distributed Heat Transfer
- Aids in Efficient Utilization of PC Board Area

Specifications¹

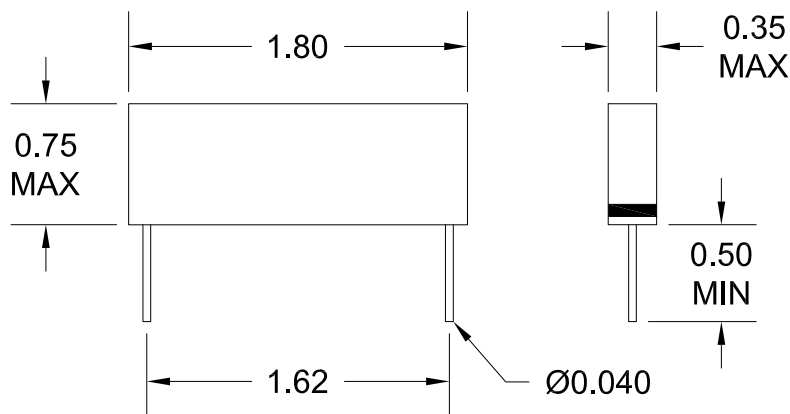
Part Number	V _{RRM} V	I _{FAVM1} mA	I _{FAVM2} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} ² nS
Standard Recovery Subseries								
HV458S8	8000	650	1200	8.0	1	50	-	-
HV458S10	10000	550	1000	10.0	1	50	-	-
HV458S12	12000	475	870	12.0	1	50	-	-
HV458S15	15000	425	780	15.0	1	50	-	-
Ultra Fast Recovery Subseries								
HV458U8	8000	425	750	20.0	1	30	4.7	75
HV458U10	10000	375	660	25.0	1	30	3.8	75
HV458U12	12000	325	570	30.0	1	30	3.2	75
HV458U15	15000	275	480	37.5	1	30	2.5	75

Temperature °C	
Storage Temperature	-55 to 150
Operating Temperature	-55 to 150

¹25°C ambient temperature unless stated otherwise.

²A "-" indicates that the component is a standard recovery device and no T_{RR} data is taken.

Drawings



Dimensions in inches, tolerances ±0.020 except as noted



HV458 SERIES

Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM1}	Maximum Average Forward Current	At T _A = 25°C
I_{FAVM2}	Maximum Average Forward Current	At T _A = 55°C, in Oil
V_F	Maximum Forward Voltage Drop	At 100mA
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3 mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 0.5 I _{FAVM1} ; I _R = - I _{FAVM1} ; I _{RR} = -0.25 I _{FAVM1}

Note: Specifications subject to change without notice. Photo is representation only.

